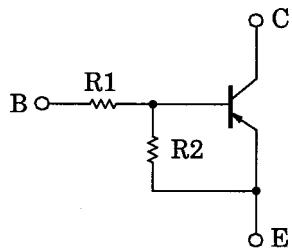


TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

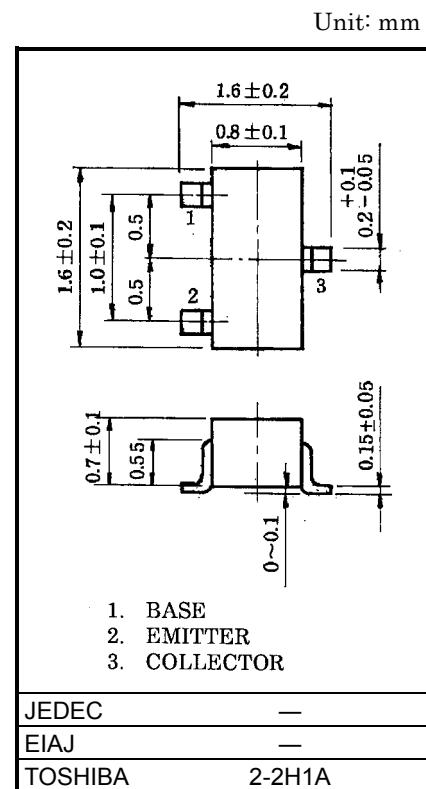
RN2107,RN2108,RN2109

Switching, Inverter Circuit, Interface Circuit
and Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1107~RN1109

Equivalent Circuit and Bias Resister Values

Type No.	R1 (kΩ)	R2 (kΩ)
RN2107	10	47
RN2108	22	47
RN2109	47	22

**Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)**

Weight: 2.4mg

Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN2107~RN2109	V _{CBO}	-50	V
Collector-emitter voltage		V _{CEO}	-50	V
Emitter-base voltage	RN2107	V _{EBO}	-6	V
	RN2108		-7	
	RN2109		-15	
Collector current	RN2107~RN2109	I _C	-100	mA
Collector power dissipation		P _{C*}	100	mW
Junction temperature		T _j	150	°C
Storage temperature range		T _{stg}	-55~150	°C

*: Total rating

Electrical Characteristics ($T_a = 25^\circ\text{C}$) (Q1, Q2 Common)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2107 ~RN2109	I_{CBO}	—	$V_{CB} = -50\text{V}, I_E = 0$	—	—	-100	nA
		I_{CEO}		$V_{CE} = -50\text{V}, I_B = 0$	—	—	-500	nA
Emitter cut-off current	RN2107	I_{EBO}	—	$V_{EB} = -6\text{V}, I_C = 0$	-0.081	—	-0.15	mA
	RN2108			$V_{EB} = -7\text{V}, I_C = 0$	-0.078	—	-0.145	
	RN2109			$V_{EB} = -15\text{V}, I_C = 0$	-0.167	—	-0.311	
DC current gain	RN2107	h_{FE}	—	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	80	—	—	—
	RN2108				80	—	—	
	RN2109				70	—	—	
Collector-emitter saturation voltage	RN2107 ~RN2109	$V_{CE} (\text{sat})$	—	$I_C = -5\text{mA}, I_B = -0.25\text{mA}$	—	-0.1	-0.3	V
Input voltage (ON)	RN2107	$V_I (\text{ON})$	—	$V_{CE} = -0.2\text{V}, I_C = -5\text{mA}$	-0.7	—	-1.8	V
	RN2108				-1.0	—	-2.6	
	RN2109				-2.2	—	-5.8	
Input voltage (OFF)	RN2107	$V_I (\text{OFF})$	—	$V_{CE} = -5\text{V}, I_C = -0.1\text{mA}$	-0.5	—	-1.0	V
	RN2108				-0.6	—	-1.16	
	RN2109				-1.5	—	-2.6	
Transition frequency	RN2107 ~RN2109	f_T	—	$V_{CE} = -10\text{V}, I_C = -5\text{mA}$	—	200	—	MHz
Collector Output capacitance	RN2107 ~RN2109	C_{ob}	—	$V_{CB} = -10\text{V}, I_E = 0,$ $f = 1\text{MHz}$	—	3	6	pF
Input resistor	RN2107	R1	—	—	7	10	13	kΩ
	RN2108				15.4	22	28.6	
	RN2109				32.9	47	61.1	
Resistor ratio	RN2107	R1/R2	—	—	0.191	0.213	0.232	—
	RN2108				0.421	0.468	0.515	
	RN2109				1.92	2.14	2.35	

